

METHOD AND SYSTEM FOR MONITORING EUV LITHOGRAPHY MASK FLATNESS

ABSTRACT OF THE DISCLOSURE

5 Disclosed are a method of and a system for monitoring extreme ultraviolet (EUV) lithography mask flatness. An EUV mask, which is chucked to a chuck, can be scanned with a capacitance probe that generates elevation data for the EUV mask. From the elevation data, a first flatness profile can be generated. In one embodiment, the EUV mask can be rotated and rescanned.

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